

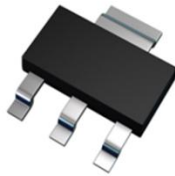
30V NPN MEDIUM POWER HIGH CURRENT TRANSISTOR IN SOT223
Features

- $BV_{CEO} > 30V$
- $I_C = 7A$ High Continuous Collector Current
- $I_{CM} = 20A$ Peak Pulse Current
- $P_D = 3W$ Power Dissipation
- Extremely Low Equivalent On-Resistance; $R_{CE(SAT)} = 36\Omega$ at 5A
- Very Low Saturation Voltages
- Complimentary PNP Type FZT949
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

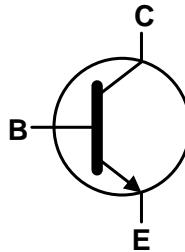
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208
- Weight: 0.112 grams (Approximate)

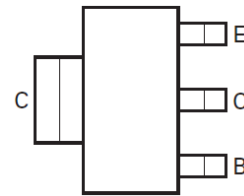
SOT223



Top View



Equivalent Circuit


 Top View
Pin-Out

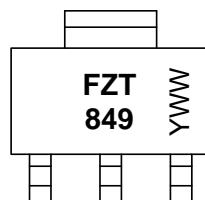
Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
FZT849TA	AEC-Q101	FZT849	7	12	1,000

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information

SOT223



FZT 849 = Product Type Marking Code
 YWW = Date Code Marking
 Y or \bar{Y} = Last Digit of Year (ex: 6 = 2016)
 WW or $\bar{W}\bar{W}$ = Week Code (01 to 53)

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	7	A
Peak Pulse Current	I _{CM}	20	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

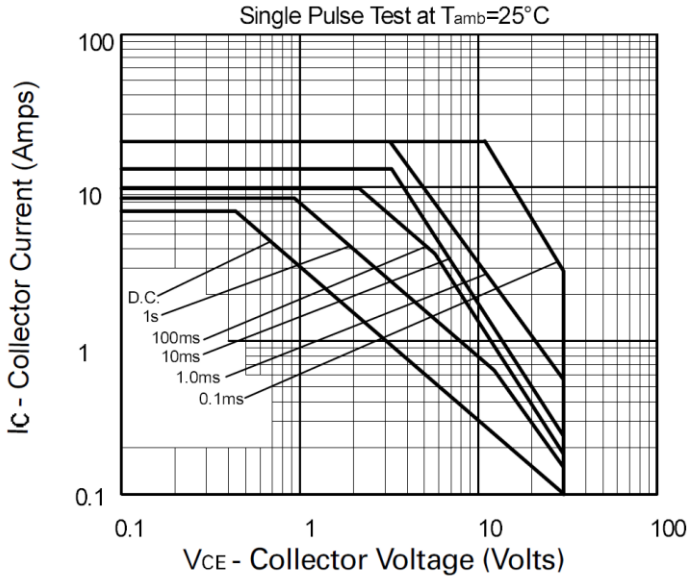
Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	3	W
		24	
Linear Derating Factor		1.6	mW/°C
		12.8	
Thermal Resistance, Junction to Ambient	R _{θJA}	42	°C/W
	R _{θJA}	78	
Thermal Resistance, Junction to Lead	R _{θJL}	8.8	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

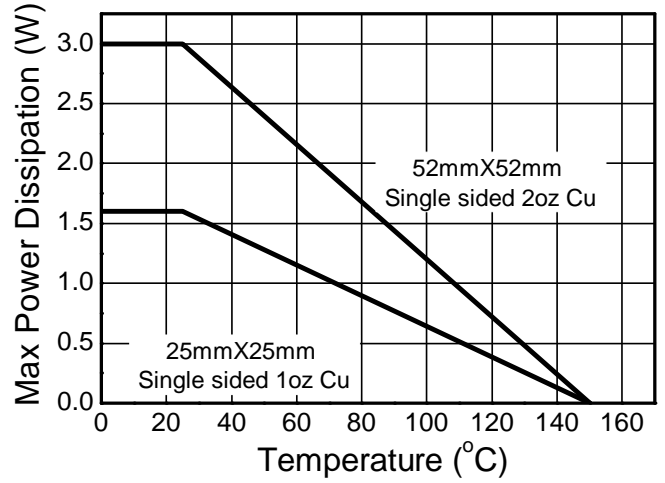
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in steady-state.
 6. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

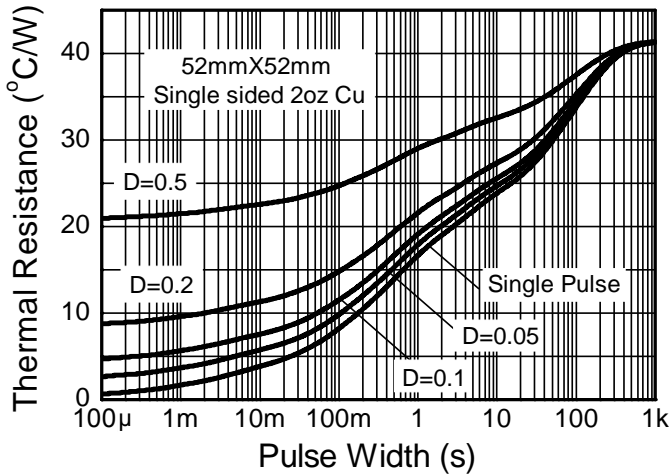
Thermal Characteristics and Derating Information



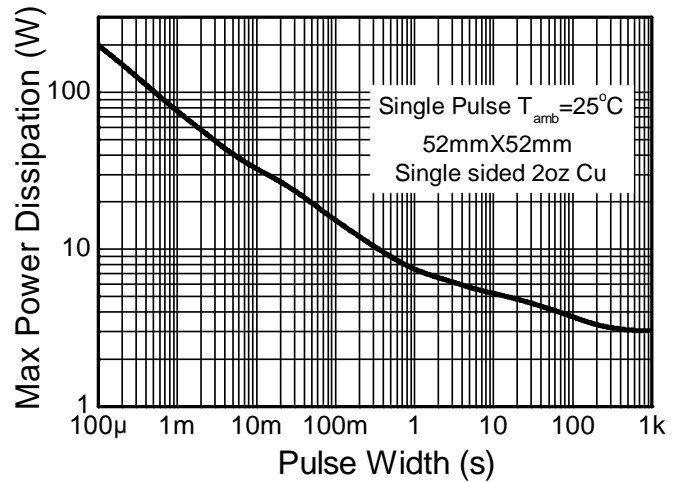
Safe Operating Area



Derating Curve



Transient Thermal Impedance



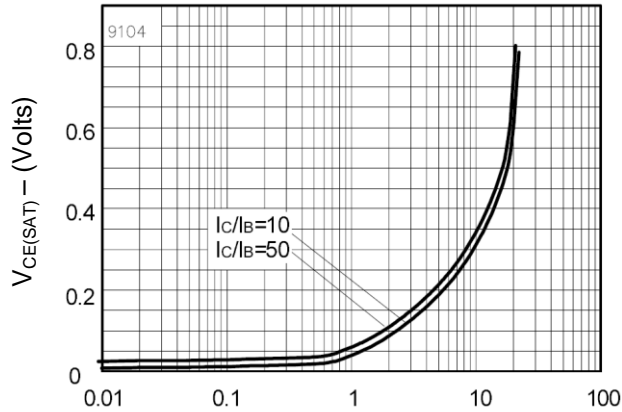
Pulse Power Dissipation

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	80	120	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage	BV_{CER}	80	120	—	V	$I_C = 1\mu\text{A}$, $R \leq 1\text{k}\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	30	40	—	V	$I_C = 10\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	6	8	—	V	$I_E = 100\mu\text{A}$
Collector-Base Cut-Off Current	I_{CBO}	—	—	50 1	nA μA	$V_{CB} = 70\text{V}$ $V_{CB} = 70\text{V}$, $T_A = +100^\circ\text{C}$
Collector Cut-Off Current	I_{CER}	—	—	50	nA	$V_{CE} = 70\text{V}$, $R \leq 1\text{k}\Omega$
		—	—	1	μA	$V_{CE} = 70\text{V}$, $R \leq 1\text{k}\Omega$, $T_A = +100^\circ\text{C}$
Emitter Cut-Off Current	I_{EBO}	—	—	10	nA	$V_{EB} = 6\text{V}$
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(SAT)}$	—	35 67 188 —	50 110 215 350	mV	$I_C = 500\text{mA}$, $I_B = 20\text{mA}$ $I_C = 1\text{A}$, $I_B = 20\text{mA}$ $I_C = 2\text{A}$, $I_B = 20\text{mA}$ $I_C = 6.5\text{A}$, $I_B = 300\text{mA}$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(SAT)}$	—	—	1.2	V	$I_C = 6.5\text{A}$, $I_B = 300\text{mA}$
Base-Emitter Turn-On Voltage (Note 9)	$V_{BE(ON)}$	—	—	1.13	V	$I_C = 6.5\text{A}$, $V_{CE} = 1\text{V}$
DC Current Gain (Note 9)	h_{FE}	100	200	—	—	$I_C = 10\text{mA}$, $V_{CE} = 1\text{V}$ $I_C = 1\text{A}$, $V_{CE} = 1\text{V}$ $I_C = 7\text{A}$, $V_{CE} = 1\text{V}$ $I_C = 20\text{A}$, $V_{CE} = 2\text{V}$
		100	200	300		
		100	150	—		
		30	65	—		
Transitional Frequency	f_T	100	—	—	MHz	$I_C = 100\text{mA}$, $V_{CE} = 10\text{V}$ $f = 50\text{MHz}$
Output Capacitance	C_{OBO}	—	75	—	pF	$V_{CB} = 10\text{V}$, $f = 1\text{MHz}$
Switching Time	t_{ON}	—	45	—	ns	$I_C = 1\text{A}$, $I_{B1} = 100\text{mA}$ $I_{B2} = -100\text{mA}$, $V_{CC} = 10\text{V}$
	t_{OFF}	—	630	—	ns	

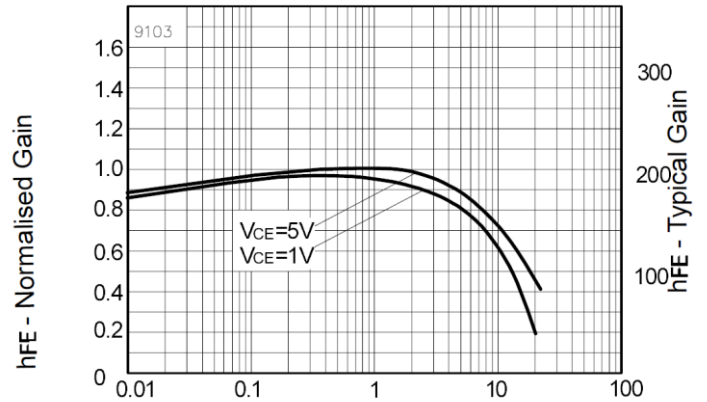
Note: 9. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



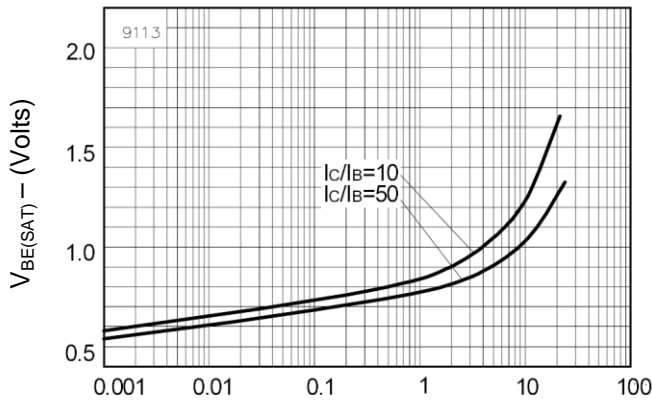
I_C - Collector Current (Amps)

$V_{CE(SAT)}$ v I_C



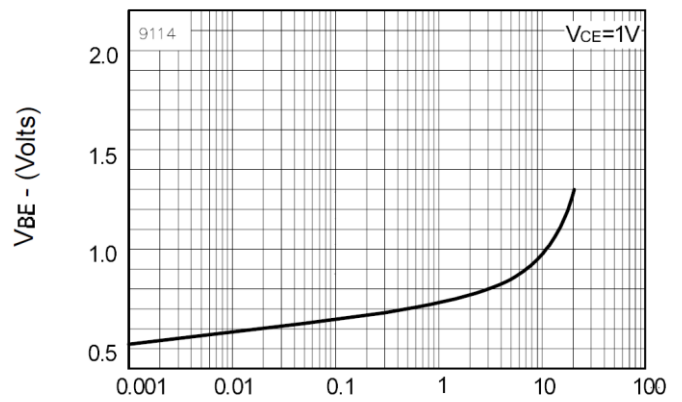
I_C - Collector Current (Amps)

hFE v I_C



I_C - Collector Current (Amps)

$V_{BE(SAT)}$ v I_C



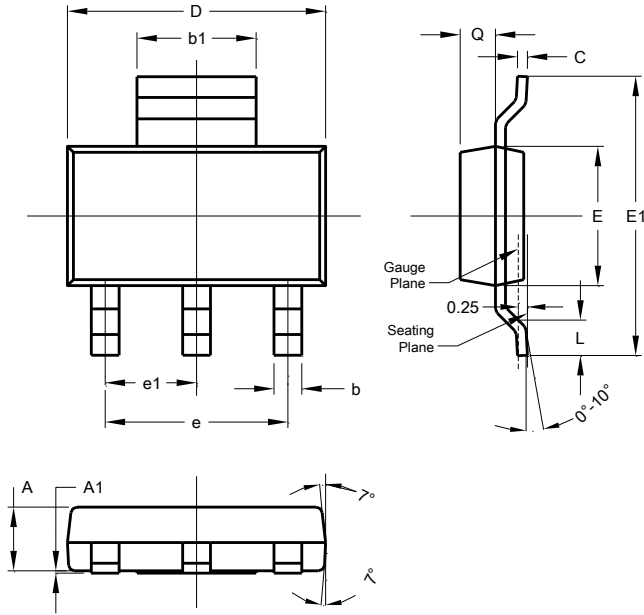
I_C - Collector Current (Amps)

$V_{BE(ON)}$ v I_C

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223

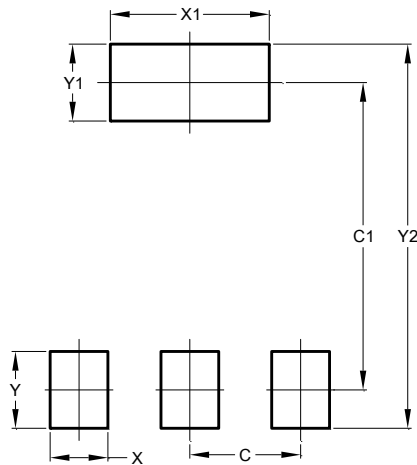


SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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